| | | | |
|---|---|---|---|
| Average gate power dissipation ($T_j$=150 ) | $P_{G(AV)}$ | 1 | W |
| Peak gate power | $P_{GM}$ | 20 | W |

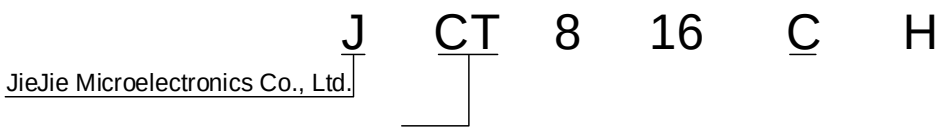

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**FIG.1:** Maximum power dissipation versus RMS on-state current

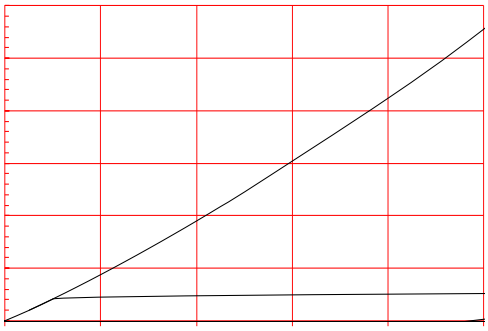
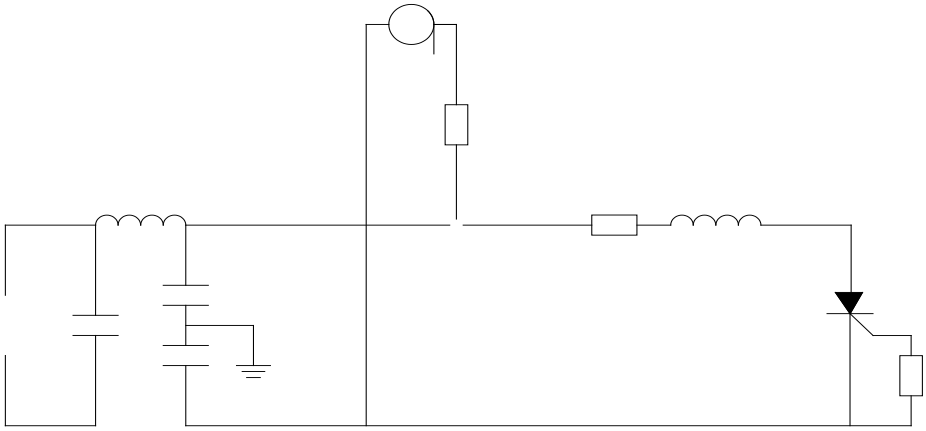


**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



| Order code | Voltage $V_{DRM}/V_{RRM}$ (V) | IGT(mA) | Package | Base qty. (pcs) | Delivery mode |
|---|---|---|---|---|---|
| JCT816CH | 800 | 15 | TO-220C | 50 | Tube |

## Document Revision History

| Date | Revision | Changes |
|---|---|---|
| Jun.15, 2023 | A. | |

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